



DOCUMENT CHANGE REQUEST

DCR number	1602	Changes required for:	General	Originator:	Steve Thacker
Date:	2024/01/12	Date sent:	2023/10/06	Organisation:	ESCC Executive Secretariat
Status:	IMPLEMENTED				

Title: TRANSISTORS, POWER, MOSFET, N-CHANNEL, RAD-HARD BASED ON TYPE STRH100N6

Number: 5205/022 Issue: 8

Other documents affected:

Page:

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Paragraph:

2.12.2

Original wording:

Source-to-Drain Diode Forward Voltage, VSD, Drift Value limit: $\pm 5\%$

Proposed wording:

Source-to-Drain Diode Forward Voltage, VSD, Drift Value limit: $\pm 15\%$

See attached spec mark-up for details.


Justification:

This DCR is raised on behalf of Manufacturer STM.

STM justification:

The latest TID result showed a drift around 10% on wafers 8 inch on VSD test.

In order to accept the wafers 8 inch, the drift value $\pm 5\%$ should be changed to $\pm 15\%$ for VSD.

Attachments:
esc5205022iss_draft_9_in_review.docx
Modifications:
N/A
Approval signature:

Date signed:
2024-01-12